

# NPN RF TRANSISTOR

**DESCRIPTION:**

The **ASI MSC80213** is a Silicon NPN Microwave Transistor Supplied in a Common Base Package, Designed for general purpose Applications up to 2.3 GHz.

**FEATURES:**

- Hermetically Sealed Package
- Gold Metallization

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	600 mA
<b>V<sub>CC</sub></b>	26 V
<b>V<sub>EB</sub></b>	3.5 V
<b>P<sub>DISS</sub></b>	11.5 W @ T <sub>C</sub> = 50 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	13 °C/W

**PACKAGE 230 2L FLG**

1 = Collector    2 = Emitter  
3 = Base

	Minimum Inches/mm	Maximum Inches/mm
A	.025/0.64	.035/0.89
B	.115/2.92 BSC	
C	.225/5.72	.235/5.97
D	.720/18.29	.750/19.05
E	.110/2.79	.120/3.05
F	.120/3.05 BSC	
G	.555/14.10	.565/14.35
H	.795/20.19	.805/20.45
I	.222/5.64	.236/5.99
J	.165/4.19	.180/4.57
K	.002/0.05	.007/0.18
L	.055/1.40	.067/1.70
M	.120/3.18	.140/3.56
N		.170/4.32

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 5.0 mA    R <sub>BE</sub> = 10Ω	44			<b>V</b>
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 1.0 mA	44			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1.0 mA	3.5			<b>V</b>
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 22 V			0.5	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V    I <sub>C</sub> = 250 mA	30		300	
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 22 V    f = 1.0 MHz			5.0	<b>pF</b>
<b>P<sub>out</sub></b>		3.8			<b>W</b>
<b>P<sub>G</sub></b>	V <sub>CC</sub> = 22 V    P <sub>IN</sub> = 0.38 W    f = 2.3 GHz	10			<b>Db</b>
<b>η<sub>C</sub></b>		40			<b>%</b>



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